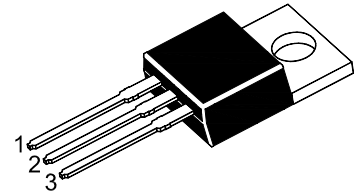


# TIP32C

## PNP Silicon Epitaxial Planar Transistor

for power switching and amplifier applications



1.Base 2.Collector 3.Emitter  
TO-220 Plastic Package

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	100	V
Collector Emitter Voltage	$-V_{CEO}$	100	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	3	A
Collector Current (Pulse)	$-I_{CP}$	5	A
Base Current	$-I_B$	1	A
Power Dissipation ( $T_a = 25\text{ }^\circ\text{C}$ )	$P_{tot}$	2	W
Power Dissipation ( $T_c = 25\text{ }^\circ\text{C}$ )	$P_{tot}$	40	W
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_s$	- 65 to + 150	$^\circ\text{C}$

### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

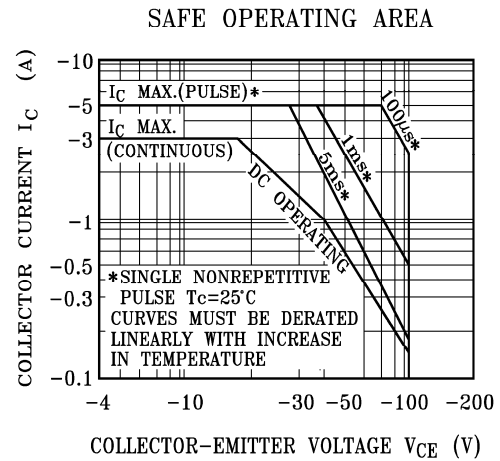
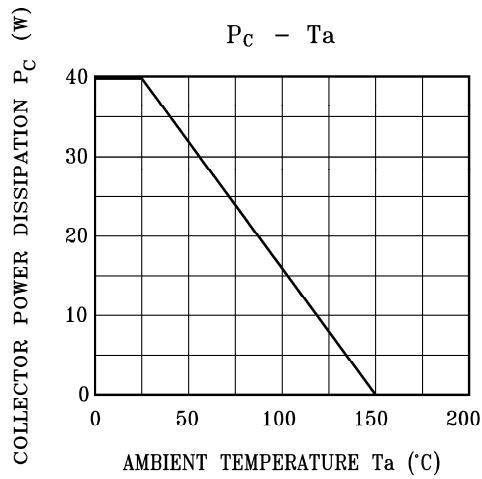
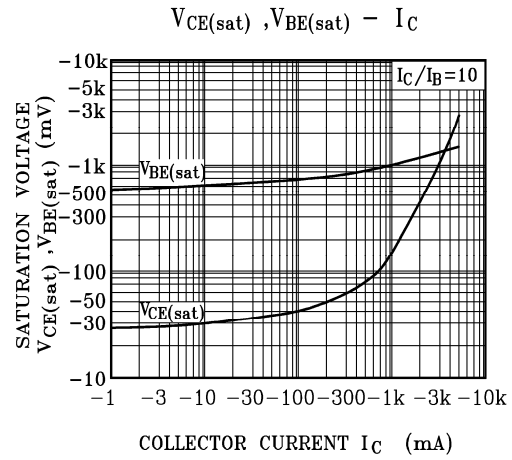
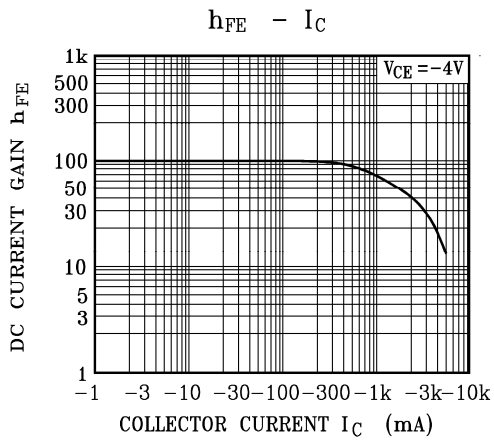
Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 4\text{ V}$ , $-I_C = 1\text{ A}$ at $-V_{CE} = 4\text{ V}$ , $-I_C = 3\text{ A}$	$h_{FE}$ $h_{FE}$	25 10	- 50	- -
Collector Emitter Sustaining Voltage at $-I_C = 30\text{ mA}$	$-V_{CEO(sus)}$	100	-	V
Collector Cutoff Current at $-V_{CE} = 100\text{ V}$	$-I_{CES}$	-	0.2	mA
Collector Cutoff Current at $-V_{CE} = 60\text{ V}$	$-I_{CEO}$	-	0.3	mA
Emitter Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	1	mA
Collector Emitter Saturation Voltage at $-I_C = 3\text{ A}$ , $-I_B = 375\text{ mA}$	$-V_{CE(sat)}$	-	1.2	V
Base Emitter On Voltage at $-V_{CE} = 4\text{ V}$ , $-I_C = 3\text{ A}$	$-V_{BE(on)}$	-	1.8	V
Transition Frequency at $-V_{CE} = 10\text{ V}$ , $-I_C = 500\text{ mA}$ , $f = 1\text{ MHz}$	$f_T$	3	-	MHz

**TOP DYNAMIC**



Dated : 21/09/2016 Rev: 01

# TIP32C

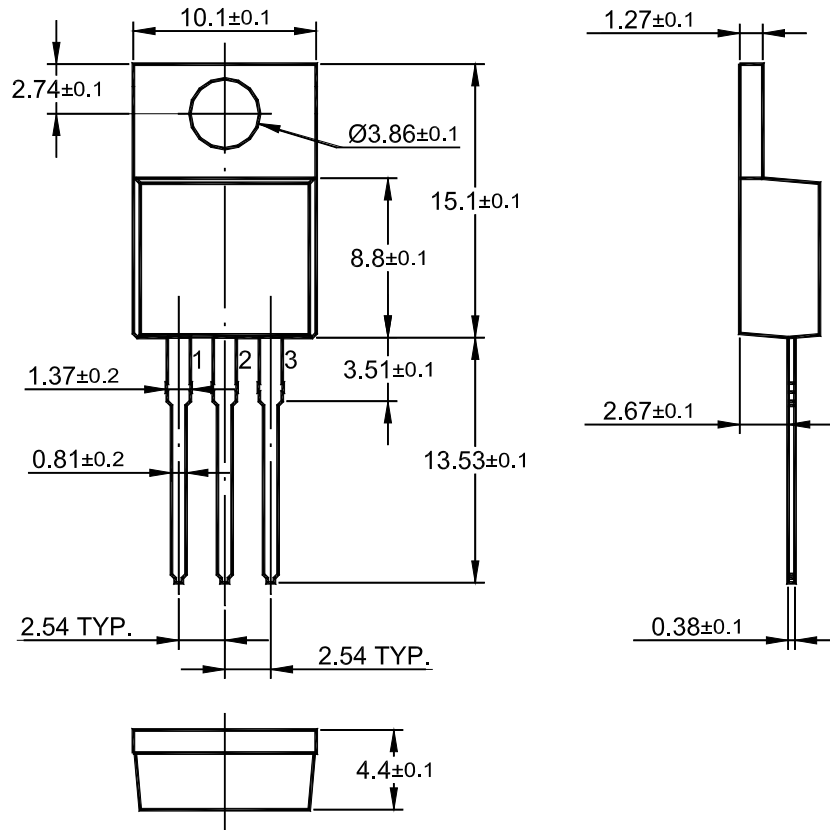


**TOP DYNAMIC**



# TIP32C

## TO-220 PACKAGE OUTLINE



Dimensions in mm

**TOP DYNAMIC**



Dated : 21/09/2016 Rev: 01